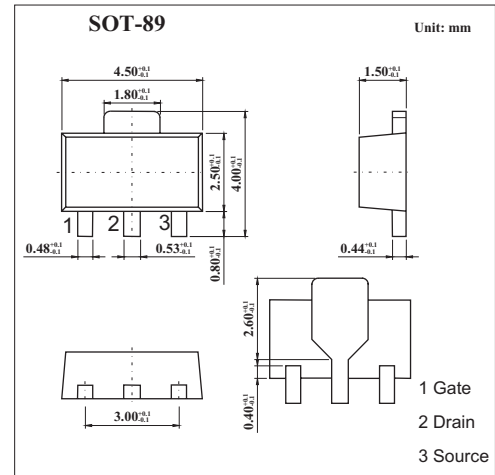
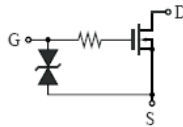


Silicon N-Channel MOSFET

2SK2211

■ Features

- Low ON-resistance $R_{DS(ON)}$
- High-speed switching



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	± 1.0	A
	I_{dp}^*	± 2.0	A
Power dissipation	P_D	1	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\text{ms}$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V_{DSS}	$I_D=0.1\text{mA}, V_{GS}=0$	30			V
Gate to source voltage	V_{GSS}	$I_{GS}=0.1\text{mA}, V_{GS}=0$	± 20			V
Drain cut-off current	I_{DSS}	$V_{DS}=25\text{V}, V_{GS}=0$			1.0	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 15\text{V}, V_{DS}=0$			± 10	μA
Gate threshold voltage	V_{th}	$V_{DS}=5\text{V}, I_D=1\text{mA}$	0.8		2	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=0.5\text{A}$	0.5			S
		$V_{GS}=4\text{V}, I_D=0.5\text{A}$		0.48	0.75	Ω
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=0.5\text{A}$		0.35	0.6	Ω
				87		pF
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		69		pF
Output capacitance	C_{oss}			23		pF
Reverse transfer capacitance	C_{rss}			12		ns
Turn-on delay time	t_{on}	$I_D=0.5\text{A}, V_{GS(on)}=10\text{V}, R_L=10\Omega, V_{DD}=10\text{V}$		160		ns
Rise time	t_r			60		ns
Turn-off delay time	t_{off}					

■ Marking

Marking	2M
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